Renesas Electronics America Inc - M3062LFGPFP#U5C Datasheet

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	M16C/60
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, IEBus, UART/USART
Peripherals	DMA, WDT
Number of I/O	85
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-BQFP
Supplier Device Package	100-QFP (14x20)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/m3062lfgpfp-u5c

1.2 Performance Outline

Table 1.1 to 1.3 list Performance Outline of M16C/62P Group (M16C/62P, M16C/62PT)(128-pin version).

Table 1.1 Performance Outline of M16C/62P Group (M16C/62P, M16C/62PT)(128-pin version)

	Item	Performance
		M16C/62P
CPU	Number of Basic Instructions	91 instructions
	Minimum Instruction Execution Time	41.7ns(f(BCLK)=24MHz, VCC1=3.3 to 5.5V) 100ns(f(BCLK)=10MHz, VCC1=2.7 to 5.5V)
	Operating Mode	Single-chip, memory expansion and microprocessor mode
	Address Space	1 Mbyte (Available to 4 Mbytes by memory space expansion function)
	Memory Capacity	See **Table 1.4 to 1.5 Product List**
Peripheral Function	Port	Input/Output : 113 pins, Input : 1 pin
	Multifunction Timer	Timer A : 16 bits x 5 channels, Timer B : 16 bits x 6 channels, Three phase motor control circuit
	Serial Interface	3 channels Clock synchronous, UART, I2C bus(1), IEBus(2) 2 channels Clock synchronous
	A/D Converter	10-bit A/D converter: 1 circuit, 26 channels
	D/A Converter	8 bits x 2 channels
	DMAC	2 channels
	CRC Calculation Circuit	CCITT-CRC
	Watchdog Timer	15 bits x 1 channel (with prescaler)
	Interrupt	Internal: 29 sources, External: 8 sources, Software: 4 sources, Priority level: 7 levels
	Clock Generation Circuit	4 circuits Main clock generation circuit (*), Subclock generation circuit (*), On-chip oscillator, PLL synthesizer (*)Equipped with a built-in feedback resistor.
	Oscillation Stop Detection Function	Stop detection of main clock oscillation, re-oscillation detection function
	Voltage Detection Circuit	Available (option(4))
Electric Characteristics	Supply Voltage	VCC1=3.0 to 5.5 V, VCC2=2.7V to VCC1 (f(BCLK=24MHz) VCC1=2.7 to 5.5 V, VCC2=2.7V to VCC1 (f(BCLK=10MHz)
	Power Consumption	14 mA (VCC1=VCC2=5V, f(BCLK)=24MHz) 8 mA (VCC1=VCC2=3V, f(BCLK)=10MHz) 1.8μA (VCC1=VCC2=3V, f(XCIN)=32kHz, wait mode) 0.7μA (VCC1=VCC2=3V, stop mode)
Flash memory version	Program/Erase Supply Voltage	3.3±0.3 V or 5.0±0.5 V
	Program and Erase Endurance	100 times (all area) or 1,000 times (user ROM area without block A and block 1) / 10,000 times (block A, block 1) (3)
Operating Ambient Temperature		-20 to 85°C, -40 to 85°C (3)
Package		128-pin plastic mold LQFP

NOTES:
1. I2C bus is a registered trademark of Koninklijke Philips Electronics N. V.
2. IEBus is a registered trademark of NEC Electronics Corporation.
3. See **Table 1.8 Product Code** for the program and erase endurance, and operating ambient temperature. In addition 1,000 times/10,000 times are under development as of Jul., 2005. Please inquire about a release schedule.
4. All options are on request basis.

1.4 Product List

Table 1.4 to 1.7 list the product list, Figure 1.3 shows the Type No., Memory Size, and Package, Table 1.8 lists the Product Code of Flash Memory version and ROMless version for M16C/62P, and Table 1.9 lists the Product Code of Flash Memory version for M16C/62PT. Figure 1.4 shows the Marking Diagram of Flash Memory version and ROM-less version for M16C/62P (Top View), and Figure 1.5 shows the Marking Diagram of Flash Memory version for M16C/62PT (Top View) at the time of ROM order.

Table 1.4 Product List (1) (M16C/62P) As of Dec. 2005

Type No.	ROM Capacity	RAM Capacity	Package Type (1)	Remarks
M30622M6P-XXXFP	48 Kbytes	4 Kbytes	PRQP0100JB-A	Mask ROM version
M30622M6P-XXXGP			PLQP0100KB-A	
M30622M8P-XXXFP	64 Kbytes	4 Kbytes	PRQP0100JB-A	
M30622M8P-XXXGP			PLQP0100KB-A	
M30623M8P-XXXGP			PRQP0080JA-A	
M30622MAP-XXXFP	96 Kbytes	5 Kbytes	PRQP0100JB-A	
M30622MAP-XXXGP			PLQP0100KB-A	
M30623MAP-XXXGP			PRQP0080JA-A	
M30620MCP-XXXFP	128 Kbytes	10 Kbytes	PRQP0100JB-A	
M30620MCP-XXXGP			PLQP0100KB-A	
M30621MCP-XXXGP			PRQP0080JA-A	
M30622MEP-XXXFP	192 Kbytes	12 Kbytes	PRQP0100JB-A	
M30622MEP-XXXGP			PLQP0100KB-A	
M30623MEP-XXXGP			PLQP0128KB-A	
M30622MGP-XXXFP	256 Kbytes	12 Kbytes	PRQP0100JB-A	
M30622MGP-XXXGP			PLQP0100KB-A	
M30623MGP-XXXGP			PLQP0128KB-A	
M30624MGP-XXXFP		20 Kbytes	PRQP0100JB-A	
M30624MGP-XXXGP			PLQP0100KB-A	
M30625MGP-XXXGP			PLQP0128KB-A	
M30622MWP-XXXFP	320 Kbytes	16 Kbytes	PRQP0100JB-A	
M30622MWP-XXXGP			PLQP0100KB-A	
M30623MWP-XXXGP			PLQP0128KB-A	
M30624MWP-XXXFP		24 Kbytes	PRQP0100JB-A	
M30624MWP-XXXGP			PLQP0100KB-A	
M30625MWP-XXXGP			PLQP0128KB-A	
M30626MWP-XXXFP		31 Kbytes	PRQP0100JB-A	
M30626MWP-XXXGP			PLQP0100KB-A	
M30627MWP-XXXGP			PLQP0128KB-A	

(D): Under development

NOTES:

1. The old package type numbers of each package type are as follows.
   PLQP0128KB-A : 128P6Q-A,
   PRQP0100JB-A : 100P6S-A,
   PLQP0100KB-A : 100P6Q-A,
   PRQP0080JA-A : 80P6S-A

Table 1.5 Product List (2) (M16C/62P) As of Dec. 2005

Type No.	ROM Capacity	RAM Capacity	Package Type (1)	Remarks
M30622MHP-XXXFP	384 Kbytes	16 Kbytes	PRQP0100JB-A	Mask ROM version
M30622MHP-XXXGP			PLQP0100KB-A	
M30623MHP-XXXGP			PLQP0128KB-A	
M30624MHP-XXXFP		24 Kbytes	PRQP0100JB-A	
M30624MHP-XXXGP			PLQP0100KB-A	
M30625MHP-XXXGP			PLQP0128KB-A	
M30626MHP-XXXFP		31 Kbytes	PRQP0100JB-A	
M30626MHP-XXXGP			PLQP0100KB-A	
M30627MHP-XXXGP			PLQP0128KB-A	
M30626MJP-XXXFP (D)	512 Kbytes	31 Kbytes	PRQP0100JB-A	
M30626MJP-XXXGP (D)			PLQP0100KB-A	
M30627MJP-XXXGP (D)			PLQP0128KB-A	
M30622F8PFP	64K+4 Kbytes	4 Kbytes	PRQP0100JB-A	Flash memory version (2)
M30622F8PGP			PLQP0100KB-A	
M30623F8PGP			PRQP0080JA-A	
M30620FCPFP	128K+4 Kbytes	10 Kbytes	PRQP0100JB-A	
M30620FCPGP			PLQP0100KB-A	
M30621FCPGP			PRQP0080JA-A	
M3062LFGPFP(3) (D)	256K+4 Kbytes	20 Kbytes	PRQP0100JB-A	
M3062LFGPGP(3) (D)			PLQP0100KB-A	
M30625FGPGP			PLQP0128KB-A	
M30626FHPFP	384K+4 Kbytes	31 Kbytes	PRQP0100JB-A	
M30626FHPGP			PLQP0100KB-A	
M30627FHPGP			PLQP0128KB-A	
M30626FJPFP	512K+4 Kbytes	31 Kbytes	PRQP0100JB-A	
M30626FJPGP			PLQP0100KB-A	
M30627FJPGP			PLQP0128KB-A	
M30622SPFP	–	4 Kbytes	PRQP0100JB-A	ROM-less version
M30622SPGP			PLQP0100KB-A	
M30620SPFP		10 Kbytes	PRQP0100JB-A	
M30620SPGP			PLQP0100KB-A	
M30624SPFP (D)	–	20 Kbytes	PRQP0100JB-A	
M30624SPGP (D)			PLQP0100KB-A	
M30626SPFP (D)		31 Kbytes	PRQP0100JB-A	
M30626SPGP (D)			PLQP0100KB-A	

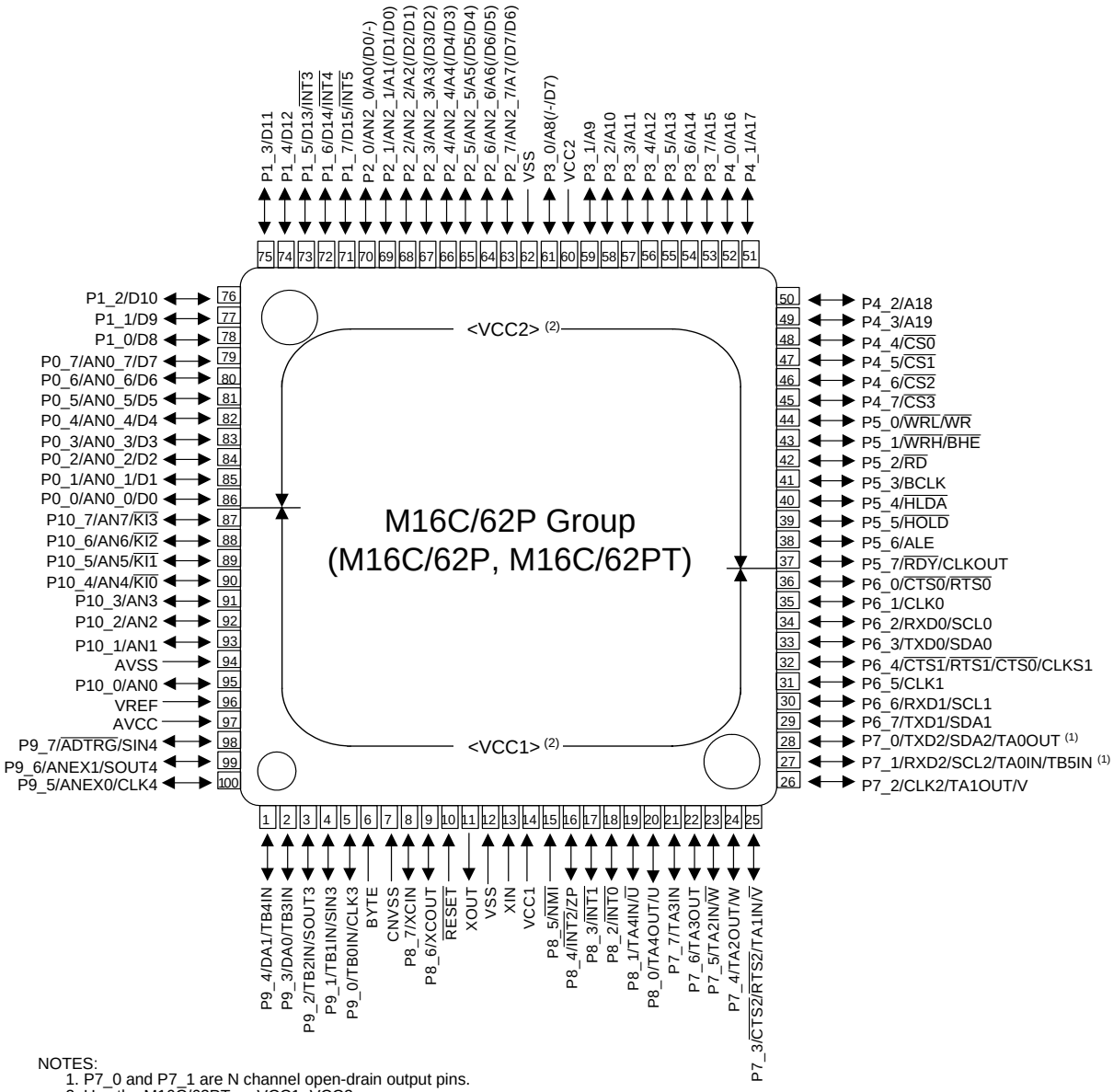
(D): Under development

NOTES:

1. The old package type numbers of each package type are as follows.
   PLQP0128KB-A : 128P6Q-A,
   PRQP0100JB-A : 100P6S-A,
   PLQP0100KB-A : 100P6Q-A,
   PRQP0080JA-A : 80P6S-A
2. In the flash memory version, there is 4K bytes area (block A).
3. Please use M3062LFGPFP and M3062LFGPGP for your new system instead of M30624FGPFP and M30624FGPGP. The M16C/62P Group (M16C/62P, M16C/62PT) hardware manual is still good for M30624FGPFP and M30624FGPGP.

M30624FGPFP	256K+4 Kbytes	20 Kbytes	PRQP0100JB-A	Flash memory version
M30624FGPGP			PLQP0100KB-A	

PIN CONFIGURATION (top view)



NOTES:
1. P7_0 and P7_1 are N channel open-drain output pins.
2. Use the M16C/62PT on VCC1=VCC2.

Package : PLQP0100KB-A (100P6Q-A)

Figure 1.8 Pin Configuration (Top View)

Table 1.13 Pin Characteristics for 100-Pin Package (1)

Pin No.		Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
FP	GP							
1	99		P9_6			SOUT4	ANEX1	
2	100		P9_5			CLK4	ANEX0	
3	1		P9_4		TB4IN		DA1	
4	2		P9_3		TB3IN		DA0	
5	3		P9_2		TB2IN	SOUT3		
6	4		P9_1		TB1IN	SIN3		
7	5		P9_0		TB0IN	CLK3		
8	6	BYTE						
9	7	CNVSS						
10	8	XCIN	P8_7					
11	9	XCOUT	P8_6					
12	10	$\overline{\text{RESET}}$						
13	11	XOUT						
14	12	VSS						
15	13	XIN						
16	14	VCC1						
17	15		P8_5	$\overline{\text{NMI}}$				
18	16		P8_4	$\overline{\text{INT2}}$	ZP			
19	17		P8_3	$\overline{\text{INT1}}$				
20	18		P8_2	$\overline{\text{INT0}}$				
21	19		P8_1		TA4IN/$\overline{\text{U}}$			
22	20		P8_0		TA4OUT/U			
23	21		P7_7		TA3IN			
24	22		P7_6		TA3OUT			
25	23		P7_5		TA2IN/$\overline{\text{W}}$			
26	24		P7_4		TA2OUT/W			
27	25		P7_3		TA1IN/$\overline{\text{V}}$	$\overline{\text{CTS2}}$/$\overline{\text{RTS2}}$		
28	26		P7_2		TA1OUT/V	CLK2		
29	27		P7_1		TA0IN/TB5IN	RXD2/SCL2		
30	28		P7_0		TA0OUT	TXD2/SDA2		
31	29		P6_7			TXD1/SDA1		
32	30		P6_6			RXD1/SCL1		
33	31		P6_5			CLK1		
34	32		P6_4			$\overline{\text{CTS1}}$/$\overline{\text{RTS1}}$/$\overline{\text{CTS0}}$/CLKS1		
35	33		P6_3			TXD0/SDA0		
36	34		P6_2			RXD0/SCL0		
37	35		P6_1			CLK0		
38	36		P6_0			$\overline{\text{CTS0}}$/$\overline{\text{RTS0}}$		
39	37		P5_7					$\overline{\text{RDY}}$/CLKOUT
40	38		P5_6					ALE
41	39		P5_5					$\overline{\text{HOLD}}$
42	40		P5_4					$\overline{\text{HLAD}}$
43	41		P5_3					BCLK
44	42		P5_2					$\overline{\text{RD}}$
45	43		P5_1					$\overline{\text{WRH}}$/$\overline{\text{BHE}}$
46	44		P5_0					$\overline{\text{WRL}}$/$\overline{\text{WR}}$
47	45		P4_7					$\overline{\text{CS3}}$
48	46		P4_6					$\overline{\text{CS2}}$
49	47		P4_5					$\overline{\text{CS1}}$
50	48		P4_4					$\overline{\text{CS0}}$

2.8.8 Stack Pointer Select Flag (U Flag)

ISP is selected when the U flag is “0”; USP is selected when the U flag is “1”.
The U flag is cleared to “0” when a hardware interrupt request is accepted or an INT instruction for software interrupt Nos. 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is configured with three bits, for specification of up to eight processor interrupt priority levels from level 0 to level 7.
If a requested interrupt has priority greater than IPL, the interrupt is enabled.

2.8.10 Reserved Area

When write to this bit, write “0”. When read, its content is indeterminate.

5. Electrical Characteristics

5.1 Electrical Characteristics (M16C/62P)

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter		Condition	Rated Value	Unit
V_{CC1}, V_{CC2}	Supply Voltage		V_{CC1}=AVcc	–0.3 to 6.5	V
V_{CC2}	Supply Voltage		V_{CC2}	–0.3 to V_{CC1}+0.1	V
AVcc	Analog Supply Voltage		V_{CC1}=AVcc	–0.3 to 6.5	V
V_I	Input Voltage	$\overline{\text{RESET}}$, CNVSS, BYTE, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, VREF, XIN		–0.3 to V_{CC1}+0.3 (1)	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		–0.3 to V_{CC2}+0.3 (1)	V
		P7_0, P7_1		–0.3 to 6.5	V
V_O	Output Voltage	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, XOUT		–0.3 to V_{CC1}+0.3 (1)	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		–0.3 to V_{CC2}+0.3 (1)	V
		P7_0, P7_1		–0.3 to 6.5	V
P_d	Power Dissipation		–40°C<T_{opr}≤85°C	300	mW
T_{opr}	Operating Ambient Temperature	When the Microcomputer is Operating		–20 to 85 / –40 to 85	°C
		Flash Program Erase		0 to 60	
T_{stg}	Storage Temperature			–65 to 150	°C

NOTES:
1. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.

Table 5.6 Flash Memory Version Electrical Characteristics (1) for 100 cycle products (D3, D5, U3, U5)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3)		100			cycle
–	Word Program Time (V_{CC1}=5.0V)			25	200	µs
–	Lock Bit Program Time			25	200	µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block		0.3	4	s
–		8-Kbyte block		0.3	4	s
–		32-Kbyte block		0.5	4	s
–		64-Kbyte block		0.8	4	s
–	Erase All Unlocked Blocks Time (2)				4×n	s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		10			year

Table 5.7 Flash Memory Version Electrical Characteristics (6) for 10,000 cycle products (D7, D9, U7, U9) (Block A and Block 1 (7))

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3, 8, 9)		10,000 (4)			cycle
–	Word Program Time (V_{CC1}=5.0V)			25		µs
–	Lock Bit Program Time			25		µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block		0.3		s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		10			year

NOTES:
1. Referenced to V_{CC1}=4.5 to 5.5V, 3.0 to 3.6V at Topr = 0 to 60 °C (D3, D5, U3, U5) unless otherwise specified.
2. n denotes the number of block erases.
3. Program and Erase Endurance refers to the number of times a block erase can be performed.
   If the program and erase endurance is n (n=100, 1,000, or 10,000), each block can be erased n times.
   For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
4. Maximum number of E/W cycles for which operation is guaranteed.
5. Topr = -40 to 85 °C (D3, D7, U3, U7) / -20 to 85 °C (D5, D9, U5, U9).
6. Referenced to V_{CC1} = 4.5 to 5.5V, 3.0 to 3.6V at T_{opr} = -40 to 85 °C (D7, U7) / -20 to 85 °C (D9, U9) unless otherwise specified.
7. Table 5.7 applies for block A or block 1 program and erase endurance > 1,000. Otherwise, use Table 5.6.
8. To reduce the number of program and erase endurance when working with systems requiring numerous rewrites, write to unused word addresses within the block instead of rewrite. Erase block only after all possible addresses are used. For example, an 8-word program can be written 256 times maximum before erase becomes necessary.
   Maintaining an equal number of erasure between block A and block 1 will also improve efficiency. It is important to track the total number of times erasure is used.
9. Should erase error occur during block erase, attempt to execute clear status register command, then block erase command at least three times until erase error disappears.
10. Set the PM17 bit in the PM1 register to “1” (wait state) when executing more than 100 times rewrites (D7, D9, U7 and U9).
11. Customers desiring E/W failure rate information should contact their Renesas technical support representative.

Table 5.8 Flash Memory Version Program / Erase Voltage and Read Operation Voltage Characteristics (at T_{opr} = 0 to 60 °C(D3, D5, U3, U5), T_{opr} = -40 to 85 °C(D7, U7) / T_{opr} = -20 to 85 °C(D9, U9))

Flash Program, Erase Voltage	Flash Read Operation Voltage
V_{CC1} = 3.3 V ± 0.3 V or 5.0 V ± 0.5 V	V_{CC1}=2.7 to 5.5 V

Table 5.9 Low Voltage Detection Circuit Electrical Characteristics

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det4}	Low Voltage Detection Voltage (1)	V_{CC1}=0.8V to 5.5V	3.3	3.8	4.4	V
V_{det3}	Reset Level Detection Voltage (1, 2)		2.2	2.8	3.6	V
V_{det4}-V_{det3}	Electric potential difference of Low Voltage Detection and Reset Level Detection		0.3			V
V_{det3s}	Low Voltage Reset Retention Voltage				0.8	V
V_{det3r}	Low Voltage Reset Release Voltage (3)		2.2	2.9	4.0	V

NOTES:
1. $V_{det4} > V_{det3}$.
2. Where reset level detection voltage is less than 2.7 V, if the supply power voltage is greater than the reset level detection voltage, the microcomputer operates with f(BCLK) ≤ 10MHz.
3. $V_{det3r} > V_{det3}$ is not guaranteed.
4. The voltage detection circuit is designed to use when VCC1 is set to 5V.

Table 5.10 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for Internal Power Supply Stabilization During Powering-On	V_{CC1}=2.7V to 5.5V			2	ms
$t_{d(R-S)}$	STOP Release Time				150	µs
$t_{d(W-S)}$	Low Power Dissipation Mode Wait Mode Release Time				150	µs
$t_{d(S-R)}$	Brown-out Detection Reset (Hardware Reset 2) Release Wait Time	V_{CC1}=V_{det3r} to 5.5V		6 (1)	20	ms
$t_{d(E-A)}$	Low Voltage Detection Circuit Operation Start Time	V_{CC1}=2.7V to 5.5V			20	µs

NOTES:
1. When V_{CC1} = 5V.

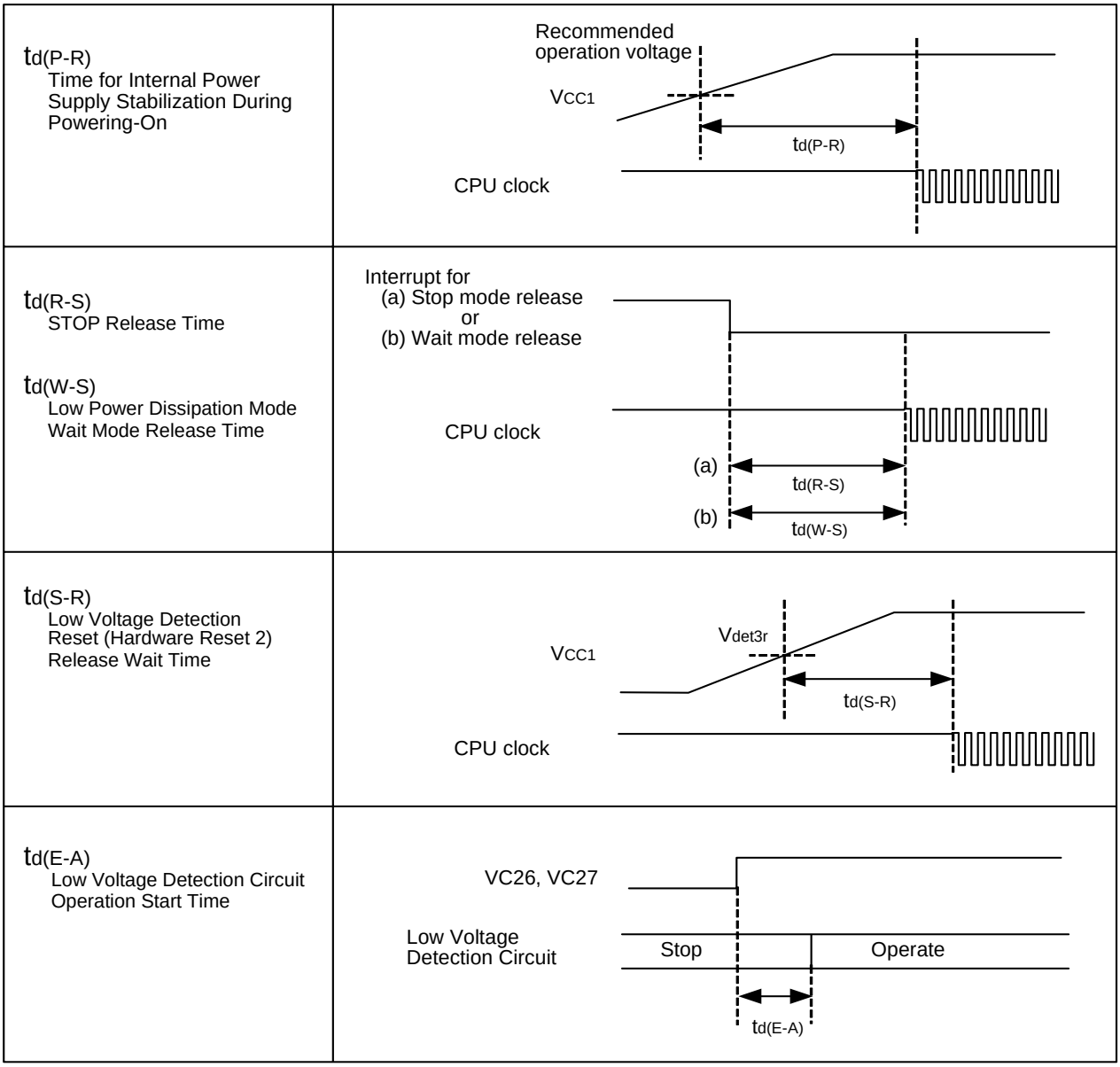


Figure 5.1 Power Supply Circuit Timing Diagram

$V_{CC1}=V_{CC2}=5V$

Switching Characteristics

(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.27 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
td(BCLK-AD)	Address Output Delay Time	See **Figure 5.2**		25	ns
th(BCLK-AD)	Address Output Hold Time (in relation to BCLK)		4		ns
th(RD-AD)	Address Output Hold Time (in relation to RD)		0		ns
th(WR-AD)	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
td(BCLK-CS)	Chip Select Output Delay Time			25	ns
th(BCLK-CS)	Chip Select Output Hold Time (in relation to BCLK)		4		ns
td(BCLK-ALE)	ALE Signal Output Delay Time			15	ns
th(BCLK-ALE)	ALE Signal Output Hold Time		–4		ns
td(BCLK-RD)	RD Signal Output Delay Time			25	ns
th(BCLK-RD)	RD Signal Output Hold Time		0		ns
td(BCLK-WR)	WR Signal Output Delay Time			25	ns
th(BCLK-WR)	WR Signal Output Hold Time		0		ns
td(BCLK-DB)	Data Output Delay Time (in relation to BCLK)			40	ns
th(BCLK-DB)	Data Output Hold Time (in relation to BCLK) (3)		4		ns
td(DB-WR)	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR) (3)		(NOTE 2)		ns
td(BCLK-HLDA)	HLDA Output Delay Time			40	ns

NOTES:

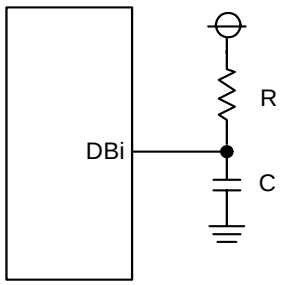
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 40[ns]$$ f(BCLK) is 12.5MHz or less.

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
   Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
   Hold time of data bus is expressed in
   $t = -CR \times \ln(1 - V_{OL} / V_{CC2})$
   by a circuit of the right figure.
   For example, when $V_{OL} = 0.2V_{CC2}$, C = 30pF, R = 1kΩ, hold time of output "L" level is
   $t = -30pF \times 1k\Omega \times \ln(1 - 0.2V_{CC2} / V_{CC2})$
   = 6.7ns.



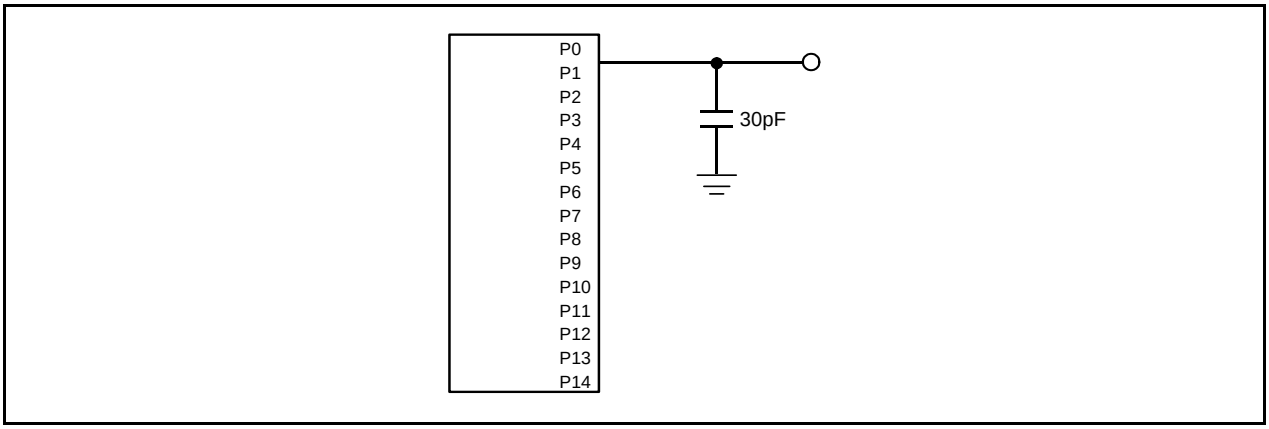


Figure 5.2 Ports P0 to P14 Measurement Circuit

$V_{CC1}=V_{CC2}=5V$

Switching Characteristics

(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.28 Memory Expansion and Microprocessor Modes (for 1- to 3-wait setting and external area access)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address Output Delay Time	See **Figure 5.2**		25	ns
$t_{h(BCLK-AD)}$	Address Output Hold Time (in relation to BCLK)		4		ns
$t_{h(RD-AD)}$	Address Output Hold Time (in relation to RD)		0		ns
$t_{h(WR-AD)}$	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
$t_{d(BCLK-CS)}$	Chip Select Output Delay Time			25	ns
$t_{h(BCLK-CS)}$	Chip Select Output Hold Time (in relation to BCLK)		4		ns
$t_{d(BCLK-ALE)}$	ALE Signal Output Delay Time			15	ns
$t_{h(BCLK-ALE)}$	ALE Signal Output Hold Time		-4		ns
$t_{d(BCLK-RD)}$	RD Signal Output Delay Time			25	ns
$t_{h(BCLK-RD)}$	RD Signal Output Hold Time		0		ns
$t_{d(BCLK-WR)}$	WR Signal Output Delay Time			25	ns
$t_{h(BCLK-WR)}$	WR Signal Output Hold Time		0		ns
$t_{d(BCLK-DB)}$	Data Output Delay Time (in relation to BCLK)			40	ns
$t_{h(BCLK-DB)}$	Data Output Hold Time (in relation to BCLK) (3)		4		ns
$t_{d(DB-WR)}$	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR)(3)		(NOTE 2)		ns
$t_{d(BCLK-HLDA)}$	HLDA Output Delay Time			40	ns

NOTES:

1. Calculated according to the BCLK frequency as follows:

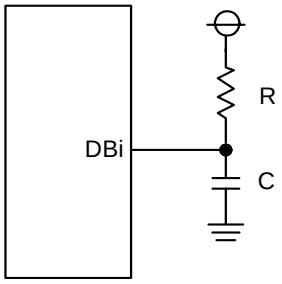
$$\frac{(n-0.5)\times 10^9}{f(BCLK)} - 40[ns]$$

n is “1” for 1-wait setting, “2” for 2-wait setting and “3” for 3-wait setting.
(BCLK) is 12.5MHz or less.

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times 10^9}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
Hold time of data bus is expressed in
$t = -CR \times \ln(1 - V_{OL} / V_{CC2})$
by a circuit of the right figure.
For example, when V_{OL} = 0.2V_{CC2}, C = 30pF, R = 1kΩ, hold time of output ”L” level is
$t = -30pF \times 1k\Omega \times \ln(1 - 0.2V_{CC2} / V_{CC2})$
= 6.7ns.



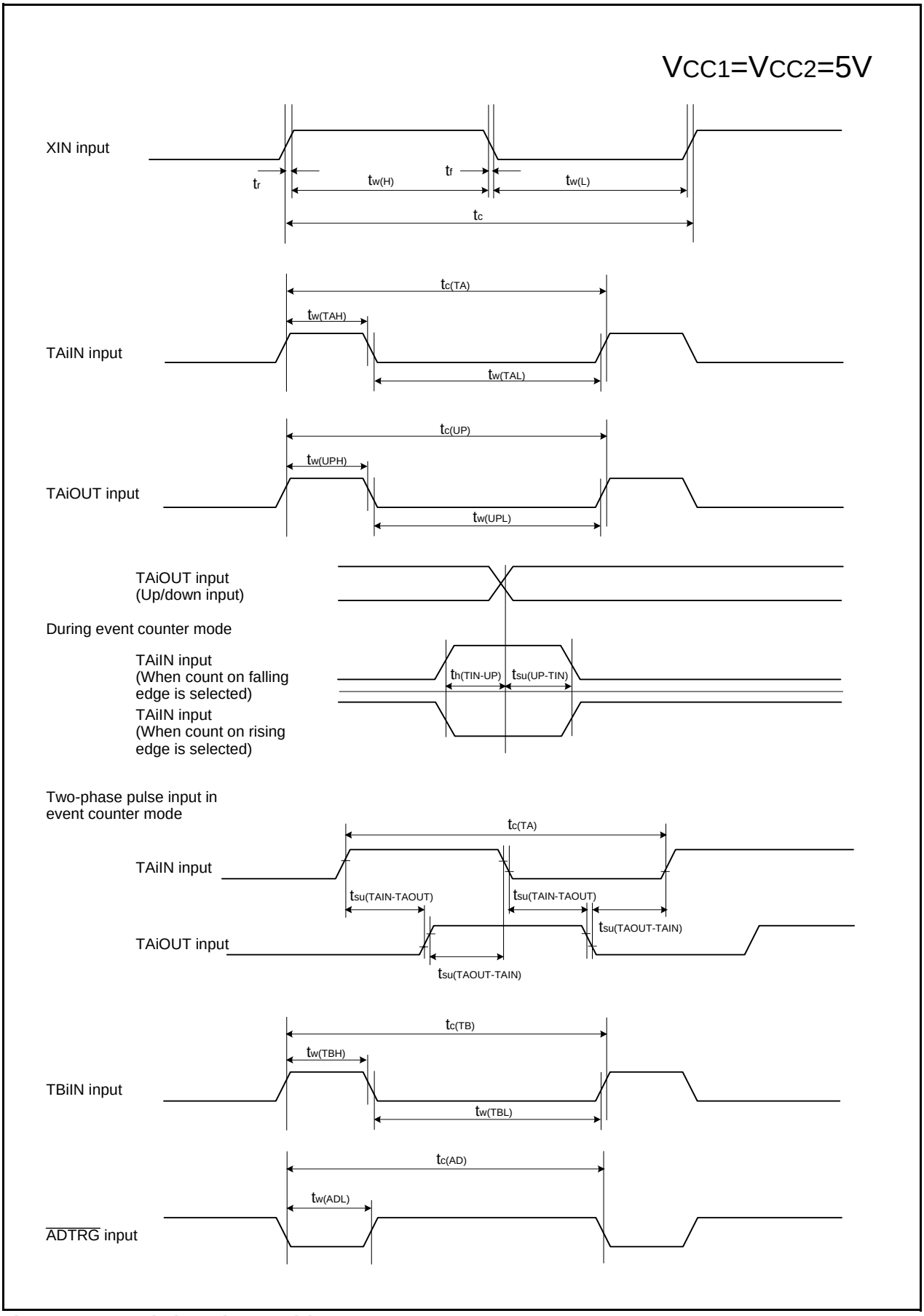
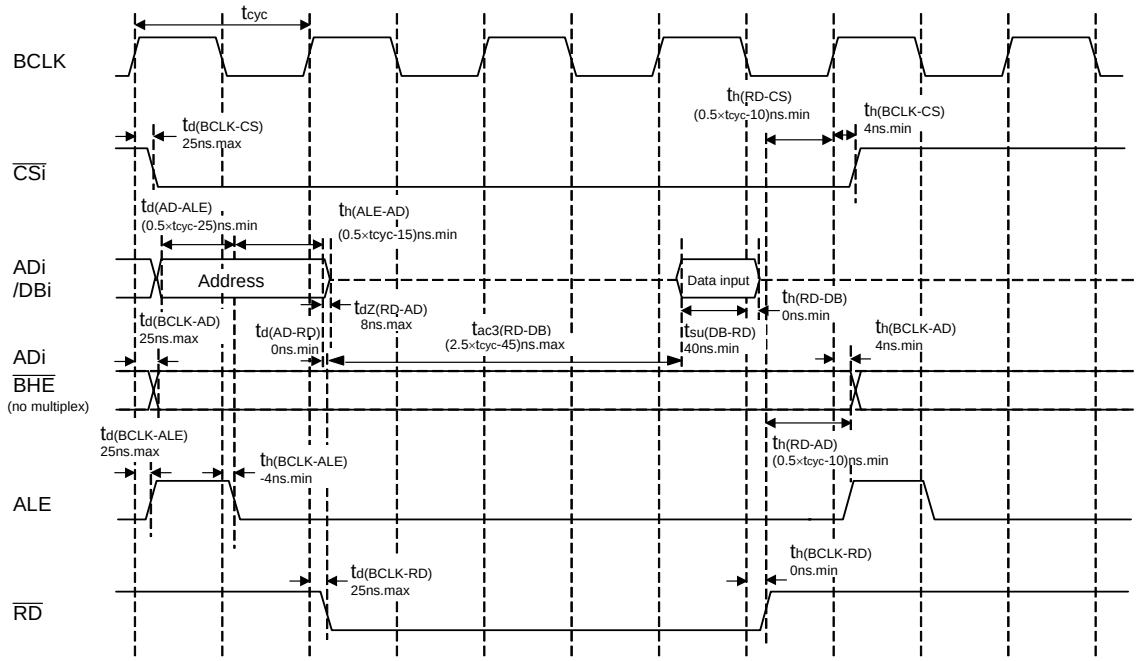


Figure 5.3 Timing Diagram (1)

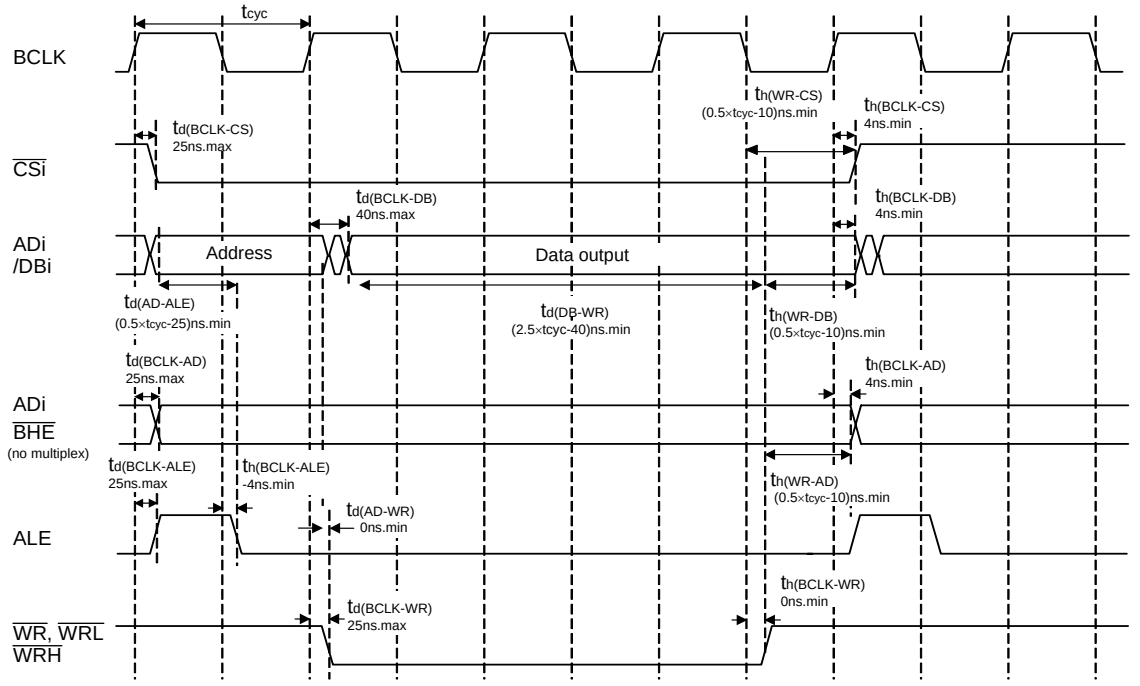
$V_{CC1}=V_{CC2}=5V$

Memory Expansion Mode, Microprocessor Mode
(For 3-wait setting, external area access and multiplex bus selection**)**

Read timing



Write timing



$$t_{cyc}=\frac{1}{f(BCLK)}$$

Measuring conditions
· $V_{CC1}=V_{CC2}=5V$
· Input timing voltage : $V_{IL}=0.8V$, $V_{IH}=2.0V$
· Output timing voltage : $V_{OL}=0.4V$, $V_{OH}=2.4V$

Figure 5.11 Timing Diagram (9)

Table 5.31 Electrical Characteristics (2) (1)

Symbol	Parameter		Measuring Condition		Standard			Unit
					Min.	Typ.	Max.	
I_{CC}	Power Supply Current (V_{CC1}=V_{CC2}=2.7V to 3.6V)	In single-chip mode, the output pins are open and other pins are V_{SS}	Mask ROM	f(BCLK)=10MHz No division		8	11	mA
				No division, On-chip oscillation		1		mA
			Flash Memory	f(BCLK)=10MHz, No division		8	13	mA
				No division, On-chip oscillation		1.8		mA
			Flash Memory Program	f(BCLK)=10MHz, VCC1=3.0V		12		mA
			Flash Memory Erase	f(BCLK)=10MHz, VCC1=3.0V		22		mA
			Mask ROM	f(XCIN)=32kHz Low power dissipation mode, ROM (3)		25		µA
			Flash Memory	f(BCLK)=32kHz Low power dissipation mode, RAM (3)		25		µA
				f(BCLK)=32kHz Low power dissipation mode, Flash Memory (3)		420		µA
				On-chip oscillation, Wait mode		45		µA
			Mask ROM Flash Memory	f(BCLK)=32kHz Wait mode (2), Oscillation capability High		6.0		µA
				f(BCLK)=32kHz Wait mode (2), Oscillation capability Low		1.8		µA
				Stop mode Topr =25°C		0.7	3.0	µA
I_{det4}	Low Voltage Detection Dissipation Current (4)					0.6	4	µA
I_{det3}	Reset Area Detection Dissipation Current (4)					0.4	2	µA

NOTES:
1. Referenced to V_{CC1}=V_{CC2}=2.7 to 3.3V, V_{SS} = 0V at T_{opr} = –20 to 85°C / –40 to 85°C, f(BCLK)=10MHz unless otherwise specified.
2. With one timer operated using fC32.
3. This indicates the memory in which the program to be executed exists.
4. I_{det} is dissipation current when the following bit is set to “1” (detection circuit enabled).

   I_{det4}: VC27 bit in the VCR2 register

   I_{det3}: VC26 bit in the VCR2 register

$V_{CC1}=V_{CC2}=3V$

Switching Characteristics

(V_{CC1} = V_{CC2} = 3V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.46 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
td(BCLK-AD)	Address Output Delay Time	See **Figure 5.12**		30	ns
th(BCLK-AD)	Address Output Hold Time (in relation to BCLK)		4		ns
th(RD-AD)	Address Output Hold Time (in relation to RD)		0		ns
th(WR-AD)	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
td(BCLK-CS)	Chip Select Output Delay Time			30	ns
th(BCLK-CS)	Chip Select Output Hold Time (in relation to BCLK)		4		ns
td(BCLK-ALE)	ALE Signal Output Delay Time			25	ns
th(BCLK-ALE)	ALE Signal Output Hold Time		–4		ns
td(BCLK-RD)	RD Signal Output Delay Time			30	ns
th(BCLK-RD)	RD Signal Output Hold Time		0		ns
td(BCLK-WR)	WR Signal Output Delay Time			30	ns
th(BCLK-WR)	WR Signal Output Hold Time		0		ns
td(BCLK-DB)	Data Output Delay Time (in relation to BCLK)			40	ns
th(BCLK-DB)	Data Output Hold Time (in relation to BCLK) (3)		4		ns
td(DB-WR)	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR) (3)		(NOTE 2)		ns
td(BCLK-HLDA)	HLDA Output Delay Time			40	ns

NOTES:

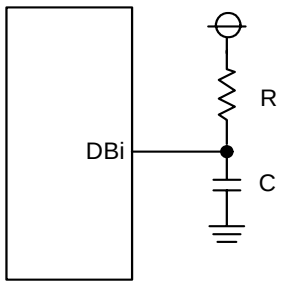
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 40[ns]$$ f(BCLK) is 12.5MHz or less.

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
   Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
   Hold time of data bus is expressed in
   $t = -CR \times \ln(1 - V_{OL} / V_{CC2})$
   by a circuit of the right figure.
   For example, when $V_{OL} = 0.2V_{CC2}$, C = 30pF, R = 1kΩ, hold time of output "L" level is
   $t = -30pF \times 1k\Omega \times \ln(1 - 0.2V_{CC2} / V_{CC2})$
   = 6.7ns.



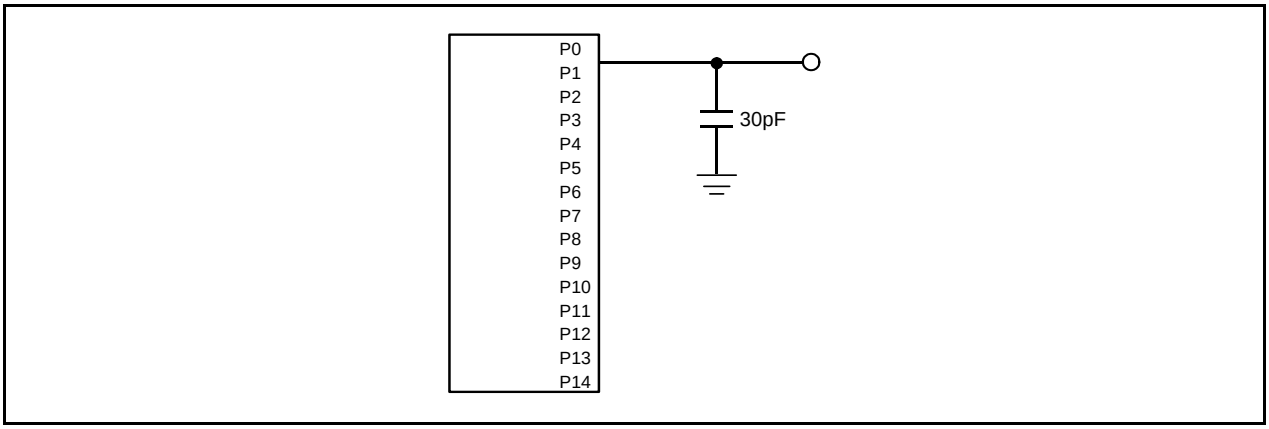


Figure 5.12 Ports P0 to P14 Measurement Circuit

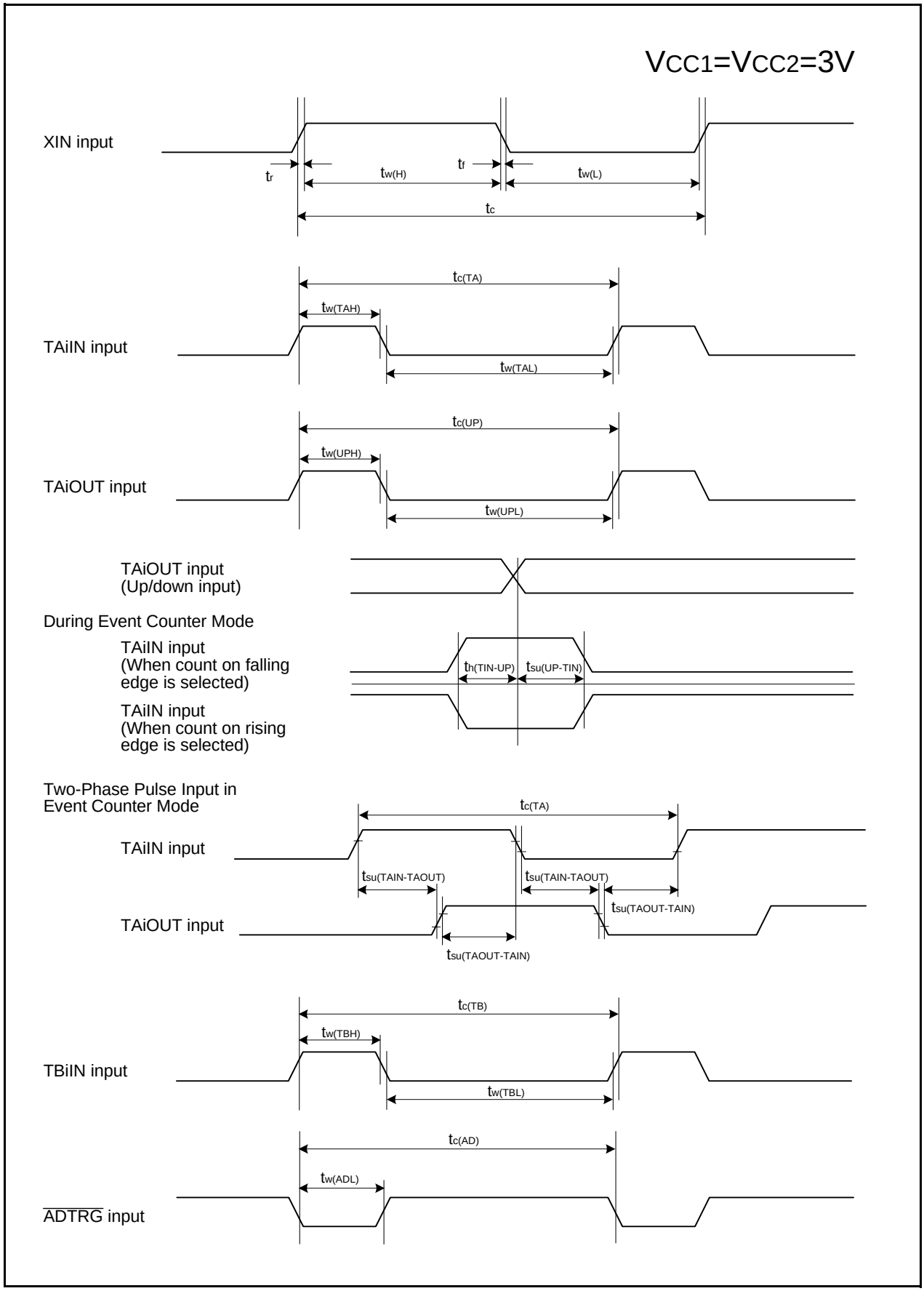


Figure 5.13 Timing Diagram (1)

Table 5.50 Recommended Operating Conditions (1) (1)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
V_{CC1}, V_{CC2}	Supply Voltage (V_{CC1} = V_{CC2})		4.0	5.0	5.5	V
AVcc	Analog Supply Voltage			V_{CC1}		V
Vss	Supply Voltage			0		V
AVss	Analog Supply Voltage			0		V
V_{IH}	HIGH Input Voltage (4)	P3_1 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	0.8V_{CC2}		V_{CC2}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (during single-chip mode)	0.8V_{CC2}		V_{CC2}	V
		P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, XIN, RESET, CNVSS, BYTE	0.8V_{CC1}		V_{CC1}	V
		P7_0, P7_1	0.8V_{CC1}		6.5	V
V_{IL}	LOW Input Voltage (4)	P3_1 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	0		0.2V_{CC2}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (during single-chip mode)	0		0.2V_{CC2}	V
		P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, XIN, RESET, CNVSS, BYTE	0		0.2Vcc	V
$I_{OH(peak)}$	HIGH Peak Output Current (4)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			–10.0	mA
$I_{OH(avg)}$	HIGH Average Output Current (4)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			–5.0	mA
$I_{OL(peak)}$	LOW Peak Output Current (4)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			10.0	mA
$I_{OL(avg)}$	LOW Average Output Current (4)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			5.0	mA
f(XIN)	Main Clock Input Oscillation Frequency	V_{CC1}=4.0V to 5.5V	0		16	MHz
f(XCIN)	Sub-Clock Oscillation Frequency			32.768	50	kHz
f(Ring)	On-chip Oscillation Frequency		0.5	1	2	MHz
f(PLL)	PLL Clock Oscillation Frequency	V_{CC1}=4.0V to 5.5V	10		24	MHz
f(BCLK)	CPU Operation Clock		0		24	MHz
t_{SU}(PLL)	PLL Frequency Synthesizer Stabilization Wait Time	V_{CC1}=5.5V			20	ms

NOTES:

1. Referenced to V_{CC1} = V_{CC2} = 4.7 to 5.5V at T_{opr} = –40 to 85°C / –40 to 125°C unless otherwise specified.
   T version = –40 to 85 °C, V version= –40 to 125 °C.
2. The Average Output Current is the mean value within 100ms.
3. The total $I_{OL(peak)}$ for ports P0, P1, P2, P8_6, P8_7, P9, P10 P1, P14_0 and P14_1 must be 80mA max. The total $I_{OL(peak)}$ for ports P3, P4, P5, P6, P7, P8_0 to P8_4, P12, and P13 must be 80mA max. The total $I_{OH(peak)}$ for ports P0, P1, and P2 must be –40mA max. The total $I_{OH(peak)}$ for ports P3, P4, P5, P12, and P13 must be –40mA max. The total $I_{OH(peak)}$ for ports P6, P7, and P8_0 to P8_4 must be –40mA max. The total $I_{OH(peak)}$ for ports P8_6, P8_7, P9 , P10, P11, P14_0, and P14_1 must be –40mA max.
   As for 80-pin version, the total $I_{OL(peak)}$ for all ports and $I_{OH(peak)}$ must be 80mA. max. due to one V_{CC} and one V_{SS}.
4. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.

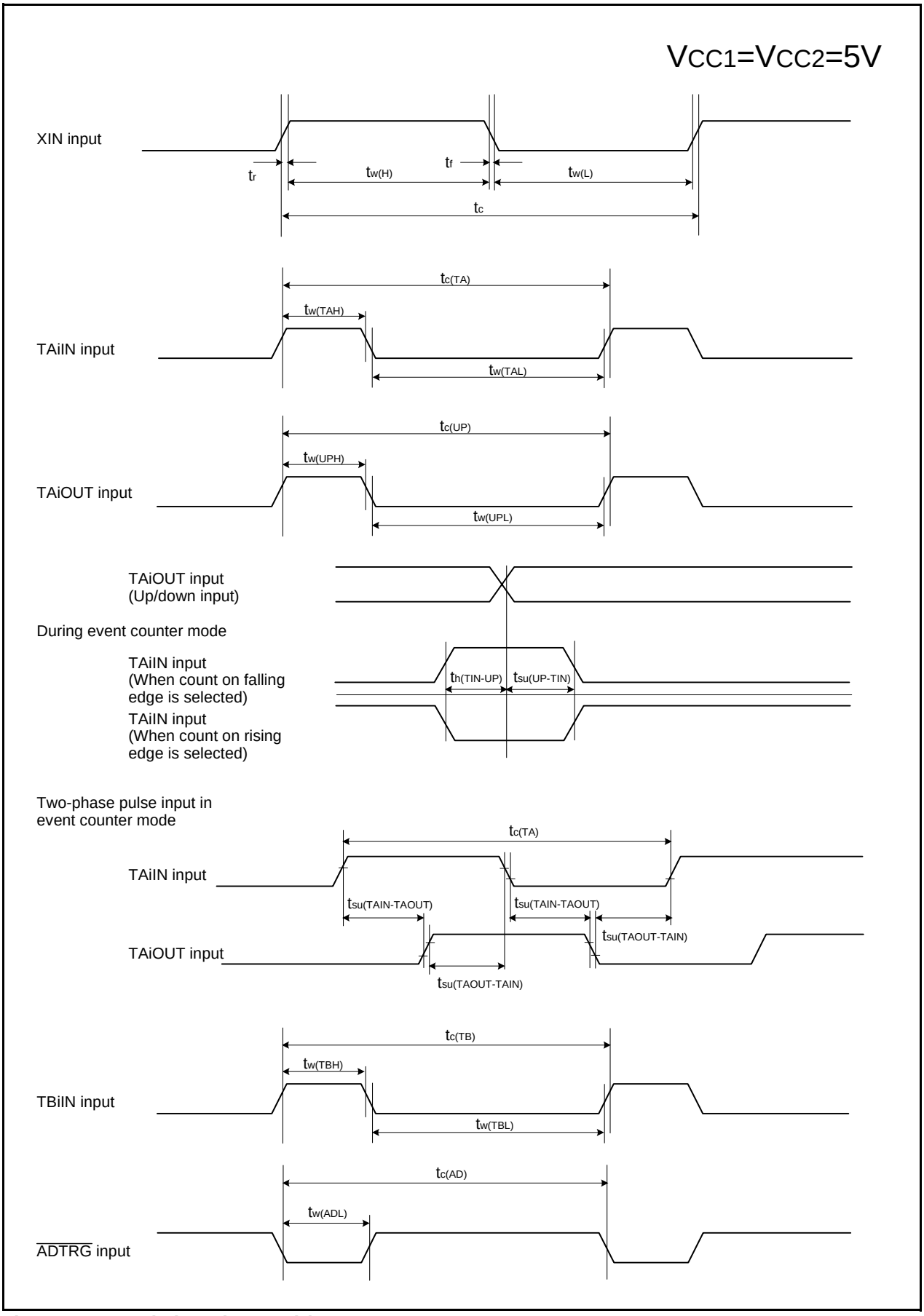


Figure 5.24 Timing Diagram (1)

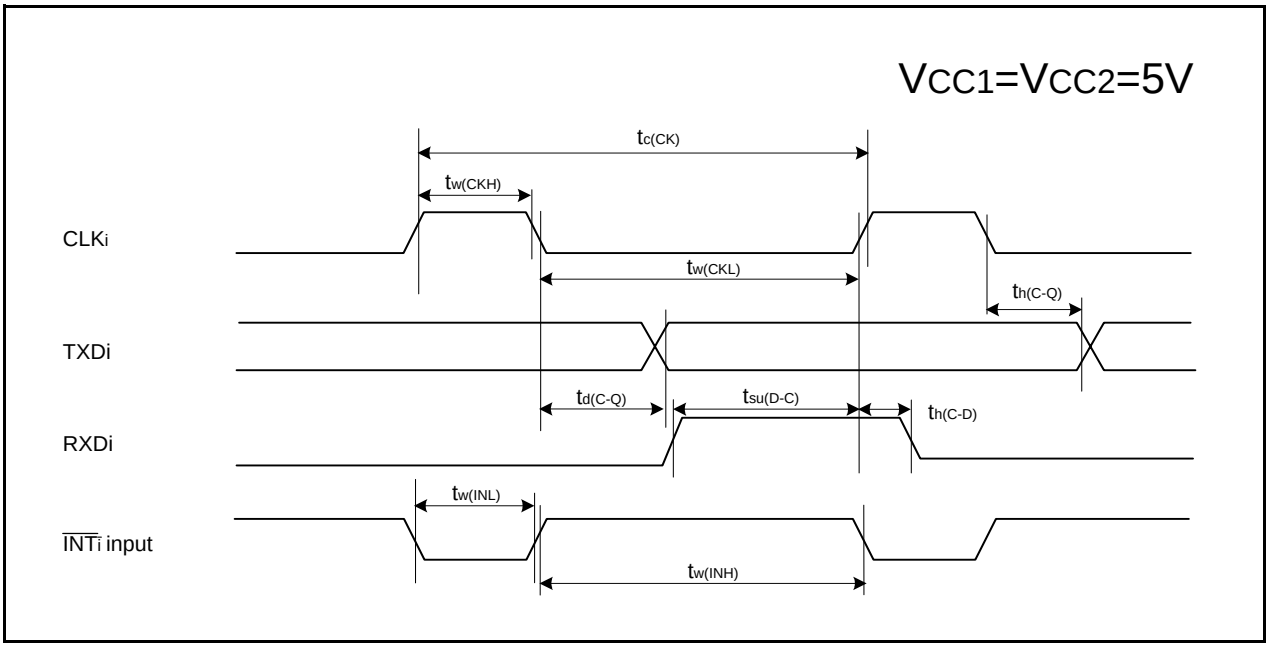


Figure 5.25 Timing Diagram (2)